

# 产品规格书

Specification of products

产品名称：三相整流桥模块

产品型号：MDS1000A-T19

浙江世菱半导体有限公司  
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

地址：浙江省 丽水市 莲都区

电话：(0578) 3012571 3615078

传真：(0578) 3611180

邮编：323000

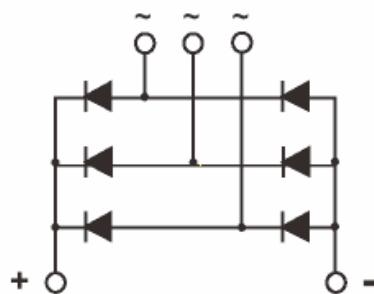
E-mail:smrshiling01@163.com

[Http://www.smrshiling.com](http://www.smrshiling.com)

拟制	审核	核准
林益龙	曹剑龙	宗瑞

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j$ (°C)	VALUE			UNIT
				Min	Type	Max	
$I_o$	DC output current	Three-phase full wave rectifying circuit, $T_c=100^\circ C$	150			1000	A
$V_{RRM}$	Repetitive peak reverse voltage	$V_{RRM}$ tp=10ms $V_{RSM}=V_{DRM}+V_{RRM}+200V$	150	600		2200	V
$I_{RRM}$	Repetitive peak current	at $V_{RRM}$	150			15	mA
$I_{FSM}$	Surge for ward current	10ms half sine wave	150			8.0	KA
$I^2t$	$I^2T$ for fusing coordination	$V_R=0.6V_{RRM}$				320	$A^2s*10^3$
$V_{FO}$	Threshold voltage		150			0.80	V
$r_F$	Forward slop resistance					1.05	mΩ
$V_{FM}$	Peak for ward voltage	$I_{FM}=1000A$	25			1.37	V
$R_{th(j-c)}$	Thermal resistance Junction to heatsink	Single side cooled				0.06	°C /W
$V_{iso}$	Isolation voltage	50Hz, R.M.S, t=1min, $I_{iso}: 1mA$ (max)		2500			V
$F_m$	Terminal connection torque(M10)				9.0		N · m
	Mounting torque( M6)				5.0		N · m
$T_{stg}$	Stored temperature			-40		125	°C
$W_t$	Weight				1050		g
Outline							

## OUTLINE DRAWING & CIRCUIT DIAGRAM



## Rating and Characteristic

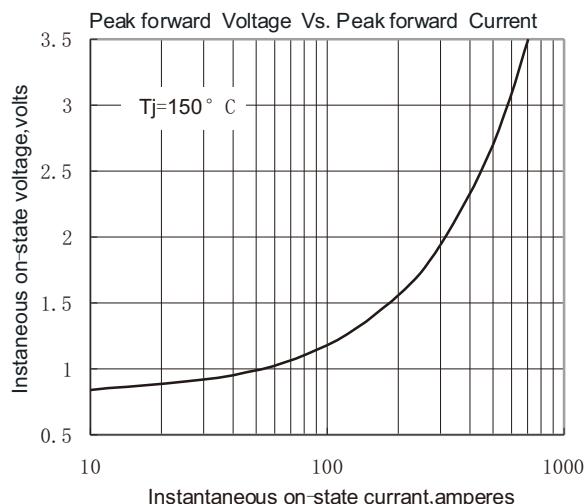


Fig. 1

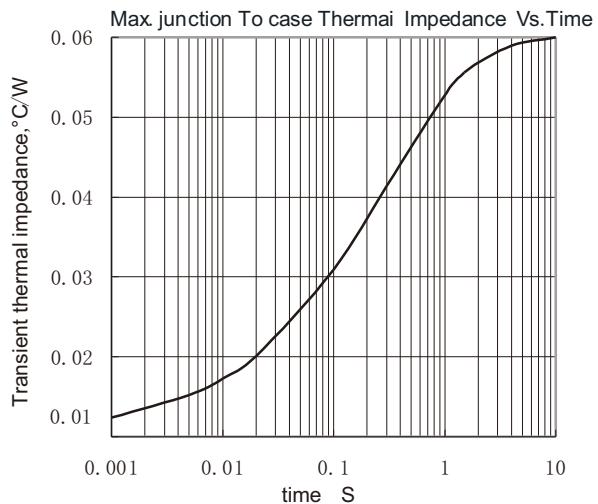


Fig. 2

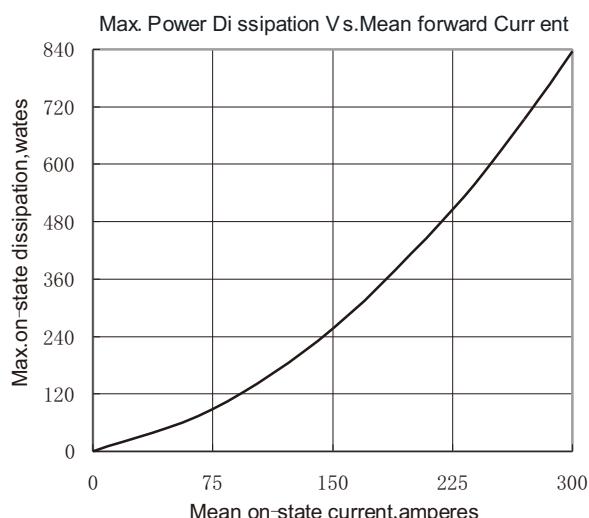


Fig. 3

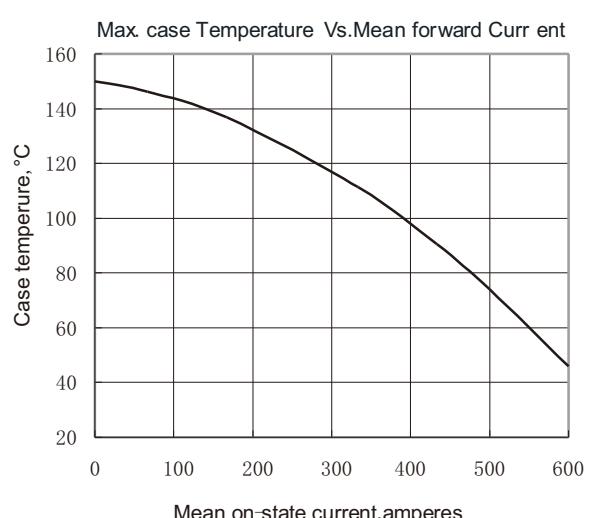


Fig. 4

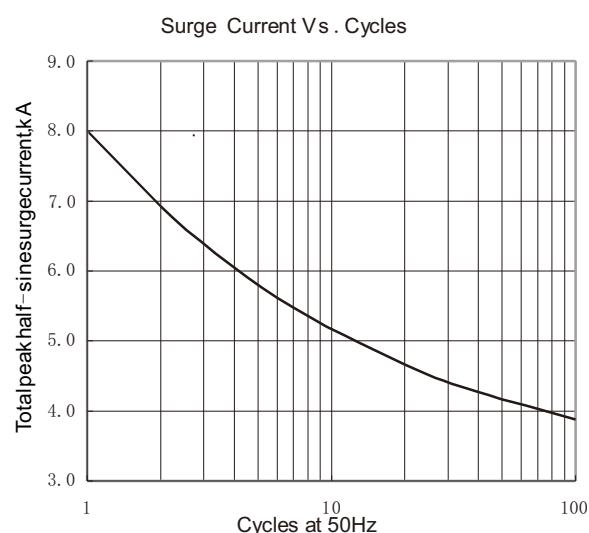


Fig. 5

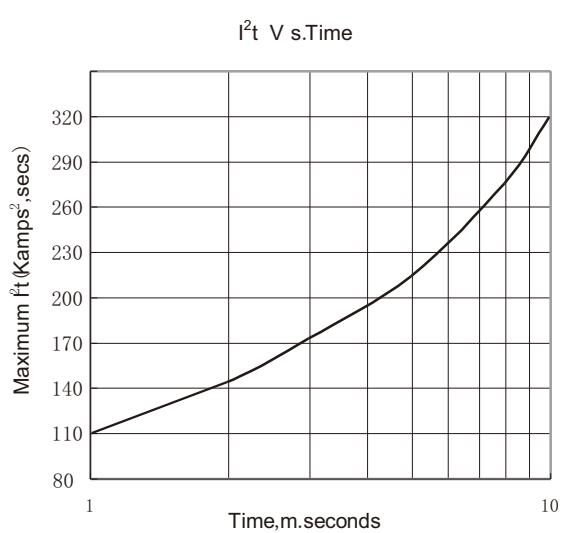


Fig. 6

## Outside Dimension

